

# Processor Supply with I<sup>2</sup>C Compatible Interface and Remote Sense

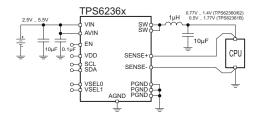
Check for Samples: TPS62360, TPS62361B, TPS62362

### **FEATURES**

- 3A Peak Output Current
- · Highest Efficiency:
  - Low R<sub>DS,on</sub> Switch and Active Rectifier
  - Power Save Mode for Light Loads
- I<sup>2</sup>C High Speed Compatible Interface
- Programmable Output Voltage for Digital Voltage Scaling
  - TPS62360/62: 0.77V to 1.4V, 10mV Steps
  - TPS62361B: 0.5V to 1.77V, 10mV Steps
- Excellent DC/AC Output Voltage Regulation
  - Differential Load Sensing
  - Precise DC Output Voltage Accuracy
  - DCS-Control<sup>™</sup> Architecture for Fast and Precise Transient Regulation
- Multiple Robust Operation/Protection Features:
  - Soft Start
  - Programmable Slew Rate at Voltage Transition
  - Over Temperature Protection
  - Input Under Voltage Detection and Lockout
- Available in 16-Bump, 2mm x 2mm NanoFree™ Package
- Low External Device Count: 27.5 mm<sup>2</sup> Solution Size

### **APPLICATIONS**

- Dynamic Voltage Scale Compliant Processors and DSPs
- SmartReflex™ Compliant Power Supply
- Cell Phones, Smart Phones, Feature Phones
- · Tablets, PDAs, MIDs, Netbooks



### DESCRIPTION

The TPS6236x are a family of high-frequency synchronous step down dc-dc converter optimized for battery-powered portable applications for a small solution size. With an input voltage range of 2.5V to 5.5V, common battery technologies are supported. The device provides up to 3A peak load current, operating at 2.5MHz typical switching frequency.

The devices convert to an output voltage range of 0.77V to 1.4V (TPS62360/62) and 0.5V to 1.77V (TPS62361B), programmable via I<sup>2</sup>C interface in 10mV steps. Dedicated inputs allow fast voltage transition to address processor performance operating points.

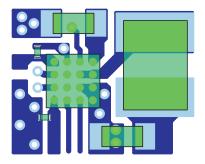
The TPS6236x supports low-voltage DSPs and processor cores in smart-phones and handheld computers including latest submicron processes. Dedicated hardware input pins allow simple transitions to performance operating points and retention modes of processors.

The devices focus on a high output voltage accuracy. The differential sensing and the DCS-Control™ architecture achieve precise static and dynamic, transient output voltage regulation.

The TPS6236x devices offer high efficiency step down conversion. The area of highest efficiency is extended towards low output currents to increase the efficiency while the processor is operating in retention mode, as well as towards highest output currents increasing the battery on-time.

The robust architecture and multiple safety features allow perfect system integration.

The 2mm x 2mm package and the low number of required external components lead to a tiny solution size of approximately 27.5 mm<sup>2</sup>.



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### ORDERING INFORMATION

PART NUMBER	PACKAGE MARKING	PACKAGE	DEVICE SPECIFIC FEATURES <sup>(1)</sup>
TPS62360 <sup>(2)</sup>	See PACKAGE SUMMARY Section	CSP-16	V <sub>OUT</sub> = 0.77V to 1.4V, 10mV Steps
TPS62361B <sup>(3)</sup>	See PACKAGE SUMMARY Section	CSP-16	V <sub>OUT</sub> = 0.5V to 1.77V, 10mV Steps
TPS62362 <sup>(4)</sup>	See PACKAGE SUMMARY Section	CSP-16	V <sub>OUT</sub> = 0.77V to 1.4V, 10mV Steps

- Contact the factory to check availability of other output voltage or feature versions.
- The YZH package is available in tape and reel. Add R suffix (TPS62360YZHR) to order quantities of 3000 parts per reel, T suffix for 250 parts per reel (TPS62360YZHT). For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder on ti.com.
- The YZH package is available in tape and reel. Add R suffix (TPS62361BYZHR) to order quantities of 3000 parts per reel, T suffix for 250 parts per reel (TPS62361BYZHT). For the most current package and ordering information, see the Package Option Addendum at the end of this document, or visit the device product folder on ti.com.
- Product preview. Please contact TI for details.

### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range (unless otherwise noted)(1)

		VA	LUE	UNIT
		MIN	MAX	UNII
	VIN, AVIN, SW pin <sup>(2)</sup>	-0.3	7	V
	EN, VSEL0, VSEL1, SENSE+(2)	-0.3	(V <sub>AVIN</sub> +0.3V)	V
Voltage range	SENSE-(2)	-0.3	0.3	V
	SCL, SDA <sup>(2)</sup>	-0.3	(V <sub>DD</sub> +0.3V)	V
	VDD <sup>(2)</sup>	-0.3	3.6	V
Continuous RMS VIN / SW current (3)			1275	mA
	Operating ambient temperature range, T <sub>A</sub> <sup>(4)</sup>	-40	85	°C
Temperature	Maximum operating junction temperature, T <sub>J (MAX)</sub>	-40	150	°C
	Storage temperature range, T <sub>stg</sub>	-65	150	°C
	Machine model		200	V
ESD rating <sup>(5)</sup>	Charge device model		500	V
	Human body model		2	kV

- (1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- All voltage values are with respect to network ground terminal.
- In order to be consistent with the TI reliability requirement for the silicon chips (100K Power-On-Hours at 105°C junction temperature), the current should not continuously exceed 1275mA in the VIN pin and 2550mA in the SW pins so as to prevent electromigration failure in the solder. See THERMAL AND DEVICE LIFE TIME INFORMATION.
- In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be derated. Maximum ambient temperature  $[T_{A(max)}]$  is dependent on the maximum operating junction temperature  $[T_{J(max)}]$ , the maximum power dissipation of the device in the application  $[P_{D(max)}]$ , and the junction-to-ambient thermal resistance of the part/package in the application  $(\theta_{JA})$ , as given by the following equation:  $T_{A(max)} = T_{J(max)} (\theta_{JA} \times P_{D(max)})$ . The human body model is a 100-pF capacitor discharged through a 1.5-k $\Omega$  resistor into each pin. The machine model is a 200-pF
- capacitor discharged directly into each pin.



### THERMAL INFORMATION

		TPS6236x	
	THERMAL METRIC <sup>(1)</sup>	YZH	UNITS
		16 PINS	
$\theta_{JA}$	Junction-to-ambient thermal resistance (2)	94.8	
$\theta_{\text{JCtop}}$	Junction-to-case (top) thermal resistance <sup>(3)</sup>	25	
$\theta_{JB}$	Junction-to-board thermal resistance <sup>(4)</sup>	60	90 AA/
ΨЈТ	Junction-to-top characterization parameter <sup>(5)</sup>	3.2	°C/W
ΨЈВ	Junction-to-board characterization parameter <sup>(6)</sup>	57	
$\theta_{JCbot}$	Junction-to-case (bottom) thermal resistance (7)	n/a	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter,  $\psi_{JT}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $\theta_{JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ<sub>JB</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

### **ELECTRICAL CHARACTERISTICS**

Unless otherwise noted the specification applies for VIN = 3.6V over an operating ambient temp.  $-40^{\circ}\text{C} \le T_A \le 85^{\circ}\text{C}$ ; Circuit of Parameter Measurement Information section (unless otherwise noted). Typical values are for  $T_A = 25^{\circ}\text{C}$ .

	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT	
INPUT						·		
V <sub>IN</sub>	Input voltage range at VIN, AVIN			2.5		5.5	٧	
$V_{DD}$	I <sup>2</sup> C and registers supply voltage range			1.15		3.6	V	
I <sub>SD(AVIN)</sub>	Shutdown current into AVIN	EN = LOW, V <sub>DI</sub>	D = 0V		0.65	5	μA	
	Object description of the MINI	EN = LOW,	T <sub>A</sub> = 25°C		0.5	1	μA	
I <sub>SD(VIN)</sub>	Shutdown current into VIN	$V_{DD} = 0V$	$T_A = 85^{\circ}C$		1	3	μA	
I <sub>SD(VDD)</sub>	Shutdown current into VDD	EN = LOW, I <sup>2</sup> C	bus idle		0.01		μA	
		EN LUCII	PFM mode		56		μA	
$I_Q$	Operating quiescent current into (AVIN + VIN)	EN = HIGH, I <sub>OUT</sub> = 0mA, not switching mode (Test Mode)		erating quiescent current into (AVIN + I <sub>OUT</sub> = 0mA, Forced PWM		180		μΑ
.,		Input voltage falling, EN = High			2.3	2.45	V	
$V_{UVLO}$	Under voltage lock out at AVIN	Input voltage rising, EN = Low			1.3		V	
V <sub>UVLO,HYST(AVI</sub>	Under voltage lock out hysteresis at AVIN	Input voltage ris	sing		110		mV	
V <sub>DD,UVLO</sub>	Under voltage lock out at VDD	Input voltage fa	Illing	0.7	0.92	1.1	V	
V <sub>UVLO,HYST(VD</sub>	Under voltage lock out hysteresis at VDD	Input voltage ris	sing		50		mV	
LOGIC INTERI	FACE					·		
V <sub>IH</sub>	High-level input voltage at EN, VSEL0, VSEL1			1.2			V	
V <sub>IL</sub>	Low-level input voltage at EN, VSEL0, VSEL1					0.4	V	
t <sub>rf</sub>	Signal transition time at EN, VSEL0, VSEL1	rising and falling edge		30			mV/μs	
V <sub>IH,I2C</sub>	High-level input voltage at SCL, SDA			0.7x V <sub>DD</sub>			V	
V <sub>IL,I2C</sub>	Low-level input voltage at SCL, SDA				(	0.3x V <sub>DD</sub>	V	



### **ELECTRICAL CHARACTERISTICS (continued)**

Unless otherwise noted the specification applies for VIN = 3.6V over an operating ambient temp.  $-40^{\circ}\text{C} \le T_{A} \le 85^{\circ}\text{C}$ ; Circuit of Parameter Measurement Information section (unless otherwise noted). Typical values are for  $T_{A} = 25^{\circ}\text{C}$ .

	PARAMETER	TEST COI	NDITIONS	MIN	TYP	MAX	UNIT
$I_{LKG}$	Logic input leakage current at EN, VSEL0, VSEL1, SDA, SCL	Internal pulldown disabled		0.05		μΑ	
$R_{PD}$	Pull down resistance at EN, VSEL0, VSEL1	Internal pulldown enabled	n resistors		300		kΩ
	I <sup>2</sup> C clock frequency	Fast mode				400	kHz
	T C clock frequency	High speed mod	le			3.4	MHz
POWER SWI	тсн					· ·	
<b>D</b>	High side MOSFET switch	$V_{IN} = 3.6V$		25	44	75	mΩ
R <sub>DS(on)</sub>	Low side MOSFET switch	$V_{IN} = 3.6V$		25	32	50	mΩ
	High side MOSFET forward current limit	V <sub>IN</sub> = 3.6V		3.0	3.6	4.3	Α
LIMF	Low side MOSFET forward current limit	V <sub>IN</sub> = 3.6V		2.6	3	3.8	Α
	Low side MOSFET negative current limit	V <sub>IN</sub> = 3.6V, PWI	/I mode	2.2	2.5	2.9	Α
SW	Nominal switching frequency	PWM mode			2.5		MHz
Γ <sub>JEW</sub>	Die temperature early warning				120		°C
JSD	Thermal shutdown				150		°C
JSD,HYST	Thermal shutdown hysteresis				20		°C
ON,min	Minimum on time				120		ns
OUTPUT		1	ļ-			<del></del>	
V <sub>OUT</sub>	Output voltage range	10mV	TPS62360/6	0.77		1.4	V
001		increments	TPS62361B	0.5		1.77	
	Output voltage accuracy	TPS62360/62: V <sub>IN</sub> = 2.5V 5.5V V <sub>OUT</sub> = 0.77V 1.4V	No load, Forced PWM, V <sub>OUT</sub> = [0.77V, 1.3V] T <sub>J</sub> = 85°C	-0.5%		+0.5%	
		TPS62361B: $V_{IN} = 2.7V$ 5.5V $V_{OUT} = 0.5V$ 1.77V	No load, Forced PWM, T <sub>J</sub> = -40 150°C	-1%	±0.5%	+1%	
	Line regulation	I <sub>OUT</sub> = 1A, force	d PWM		< 0.1		%/V
	Load regulation	$V_{OUT} = 1.2V$ , for	ced PWM		< 0.05		%/A
Start	Start-up time	Time from active EN to $V_{OUT} = 1.4V$ , $C_{OUT} < 100\mu F$ , RMP[2:0] = 000, $I_{OUT} = 0 mA$				1	ms
R <sub>Sense</sub>	Input resistance between Sense+, Sense-				2.2		МΩ
		RMP[2:0] = 000			32		
		RMP[2:0] = 001			16		
		RMP[2:0] = 010			8		
	Parent Care	RMP[2:0] = 011			4		mV/μs
	Ramp timer	RMP[2:0] = 100			2		
		RMP[2:0] = 101			1		
		RMP[2:0] = 110			0.5		
		RMP[2:0] = 111			0.25		



### I<sup>2</sup>C INTERFACE TIMING REQUIREMENTS<sup>(1)(2)</sup>

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
		Standard mode		100	kHz
		Fast mode		400	kHz
		High-speed mode (write operation), C <sub>B</sub> – 100 pF max		3.4	MHz
$f_{(SCL)}$	SCL clock frequency	High-speed mode (read operation), C <sub>B</sub> – 100 pF max		3.4	MHz
		$\begin{array}{ c c c c c c c c c c c c c c c c c c c$		1.7	MHz
		High-speed mode (read operation), C <sub>B</sub> – 400 pF max		1.7	MHz
	Bus free time between a STOP and	Standard mode	4.7		μs
t <sub>BUF</sub>	START condition	Fast mode	1.3		μs
		Standard mode	4		μs
t <sub>HD</sub> , t <sub>STA</sub>	Hold time (repeated) START condition	Fast mode	600		ns
		High-speed mode	160		ns
		Standard mode	4.7		μs
	Lawrence and a fight a COL selection	Fast mode	1.3		μs
t <sub>LOW</sub>	Low period of the SCL clock	High-speed mode, C <sub>B</sub> – 100 pF max	160		ns
		High-speed mode, C <sub>B</sub> – 400 pF max	320		ns
		Standard mode	4		μs
		Fast mode	600		ns
tHIGH	High period of the SCL clock	High-speed mode, C <sub>B</sub> – 100 pF max	60		ns
		High-speed mode, C <sub>B</sub> – 400 pF max	120		ns
		Standard mode	4.7		μs
t <sub>SU</sub> , t <sub>STA</sub>	Setup time for a repeated START condition	Fast mode	600		ns
	Condition	High-speed mode	160		ns
		Standard mode	250		ns
t <sub>SU</sub> , t <sub>DAT</sub>	Data setup time	Fast mode	100		ns
00 27.1		High-speed mode	10		ns
		Standard mode	0	3.45	μs
		Fast mode	0	0.9	μs
$t_{HD}$ , $t_{DAT}$	Data hold time	High-speed mode, C <sub>B</sub> – 100 pF max	0	70	ns
		High-speed mode, C <sub>B</sub> – 400 pF max	0	150	ns
		Standard mode	20 + 0.1 C <sub>B</sub>	1000	ns
		Fast mode	20 + 0.1 C <sub>B</sub>	300	ns
t <sub>RCL</sub>	Rise time of SCL signal	High-speed mode, C <sub>B</sub> – 100 pF max	10	40	ns
		High-speed mode, C <sub>B</sub> – 400 pF max	20	80	ns
		Standard mode	20 + 0.1 C <sub>B</sub>	1000	ns
	Rise time of SCL signal after a repeated	Fast mode	20 + 0.1 C <sub>B</sub>	300	ns
t <sub>RCL1</sub>	START condition and after an	High-speed mode, C <sub>B</sub> – 100 pF max	10	80	ns
	acknowledge bit				ns
					ns
					ns
$t_{FCL}$	Fall time of SCL signal				ns
					ns
t <sub>FCL</sub>	acknowledge bit Fall time of SCL signal	High-speed mode, C <sub>B</sub> – 100 pF max  High-speed mode, C <sub>B</sub> – 400 pF max  Standard mode  Fast mode  High-speed mode, C <sub>B</sub> – 100 pF max  High-speed mode, C <sub>B</sub> – 400 pF max	20 20 + 0.1 C <sub>B</sub> 20 + 0.1 C <sub>B</sub> 10 20	160 300 300 40 80	

 <sup>(1)</sup> S/M = standard mode; F/M = fast mode
 (2) Specified by design. Not tested in production.



# I<sup>2</sup>C INTERFACE TIMING REQUIREMENTS<sup>(1)(2)</sup> (continued)

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT
		Standard mode	20 + 0.1 C <sub>B</sub>	1000	ns
	Disc time of CDA signal	Fast mode	20 + 0.1 C <sub>B</sub>	300	ns
<sup>T</sup> RDA	t <sub>RDA</sub> Rise time of SDA signal	High-speed mode, C <sub>B</sub> – 100 pF max	10	80	ns
		High-speed mode, C <sub>B</sub> – 400 pF max	20	160	ns
	Standard mode	20 + 0.1 C <sub>B</sub>	300	ns	
		Fast mode	20 + 0.1 C <sub>B</sub>	300	ns
t <sub>FDA</sub>	Fall time of SDA signal	High-speed mode, C <sub>B</sub> – 100 pF max	10	80	ns
		High-speed mode, C <sub>B</sub> – 400 pF max	20	160	ns
		Standard mode	4		μs
$t_{SU}, t_{STO}$	Setup time for STOP condition	Fast mode	600		ns
		High-speed mode	160		ns
C <sub>B</sub>	Capacitive load for SDA and SCL			400	pF

### I<sup>2</sup>C TIMING DIAGRAMS

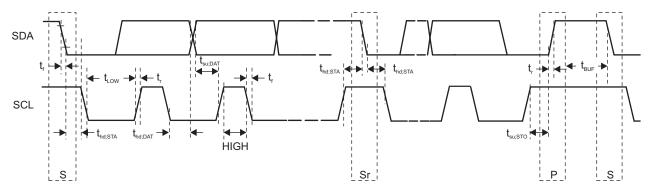
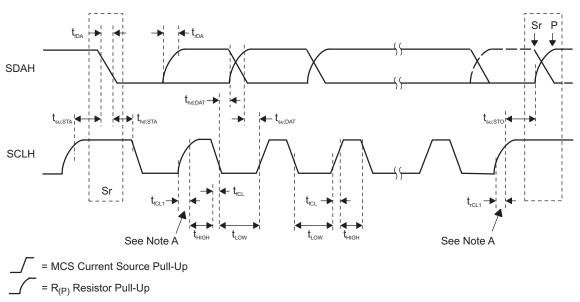


Figure 1. Serial Interface Timing for F/S Mode



Note A: First rising edge of the SCLH signal after Sr and after each acknowledge bit.

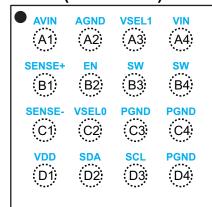
Figure 2. Serial Interface Timing for H/S Mode



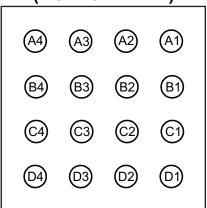
### **DEVICE INFORMATION**

### **PIN ASSIGNMENTS**

### (TOP VIEW)



### (BOTTOM VIEW)



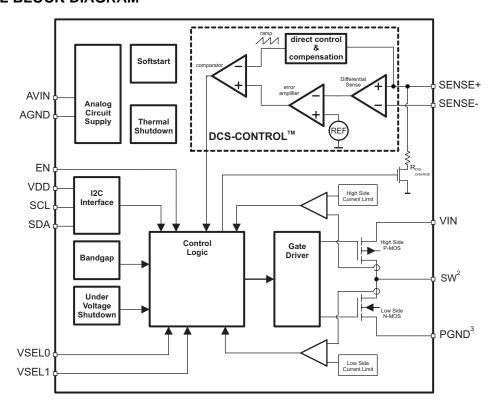
### **PIN FUNCTIONS**

PIN		1/0	DESCRIPTION				
NAME	NO.	1/0	DESCRIPTION				
AVIN	A1	I	Analog Supply Voltage Input.				
AGND	A2	_	Analog Ground Connection.				
EN	B2	I	Device Enable Logic Input. Logic HIGH enables the device, logic LOW disables the device and turns it into shutdown. The pin must be terminated to either HIGH or LOW if the internal pull down resistor is deactivated.				
VDD	D1	I	I <sup>2</sup> C Logic and Registers supply voltage. For resetting the internal registers, this connection must be pulled below its UVLO level.				
SCL	D3	I/O	I <sup>2</sup> C clock signal.				
SDA	D2	I/O	I <sup>2</sup> C data signal.				
VSEL0	C2	I	Output Settings Selection Logic Inputs. Predefined register settings can be chosen for setting output voltage and				
VSEL1	АЗ	I	mode. The pins must be terminated to logic HIGH or LOW if the internal pull down resistors are deactivated.				
SW	В3	_	Inductor connection				
SVV	В4		inductor connection				
SENSE+	B1	I	Positive Output Voltage Remote Sense. Must be connected closest to the load supply node.				
SENSE-	C1	I	Negative Output Voltage Remote Sense. Must be connected closest to the load ground node.				
VIN	A4	I	Power Supply Voltage Input.				
	СЗ	_					
PGND	C4		Power Ground Connection.				
	D4						

TEXAS INSTRUMENTS

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### **FUNCTIONAL BLOCK DIAGRAM**



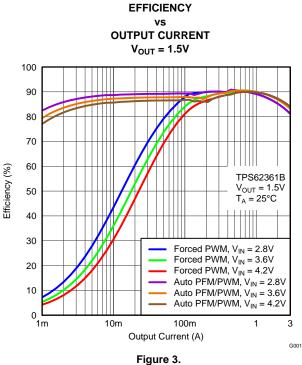


### **TYPICAL CHARACTERISTICS**

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			I <sub>OUT</sub> = 1000mA to 3000mA	Figure 31
	Line Transient Response		V <sub>IN</sub> = 3.2 to 4.2V	Figure 32
I <sub>SD(VIN)</sub> , I <sub>SD(AVIN)</sub>	Shutdown Current at AVIN and VIN	vs. Input Voltage	T <sub>A</sub> = [-40°C, 25°C, 125°C]	Figure 33
	Online and Course	Line de la control Vallacia	T <sub>A</sub> = [-40°C, 25°C, 125°C], auto PFM/PWM	Figure 34
lq	Quiescent Current	vs. Input Voltage	T <sub>A</sub> = [-40°C, 25°C, 125°C] forced PWM	Figure 35
f <sub>SW</sub>	Switching Frequency	vs. Output Current	V <sub>OUT</sub> = 1.2V	Figure 36
I <sub>LIM</sub>	Current Limit	vs. Input Voltage		Figure 37

### TYPICAL CHARACTERISTICS (continued)





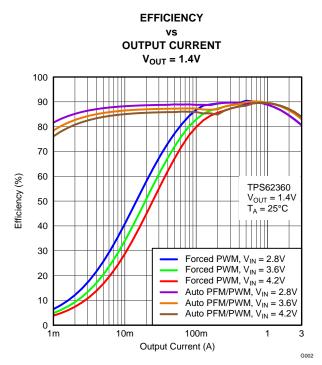
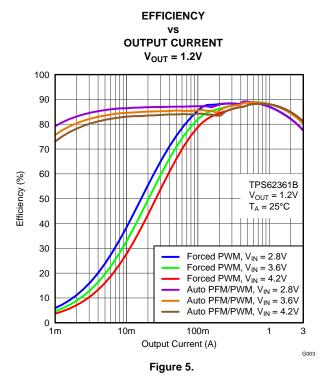


Figure 4.



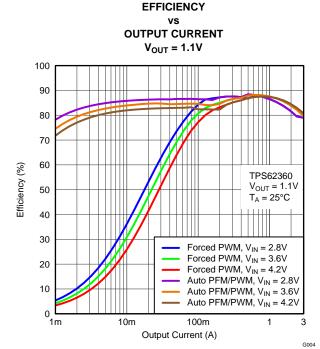
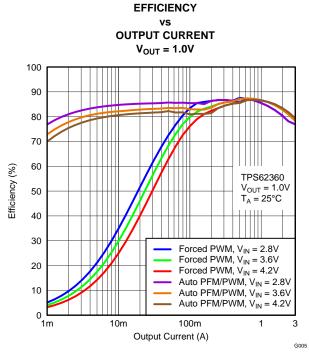
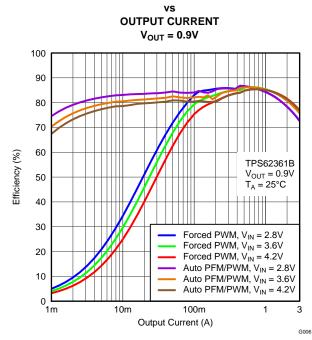


Figure 6.



### TYPICAL CHARACTERISTICS (continued)

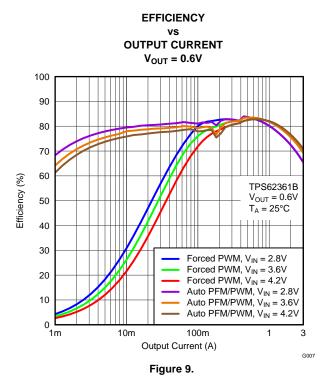


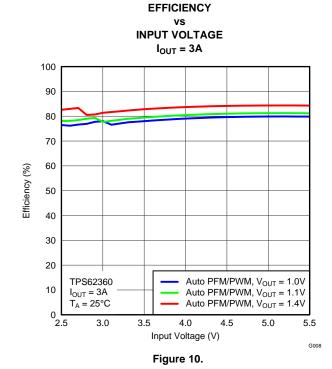


**EFFICIENCY** 

Figure 7.

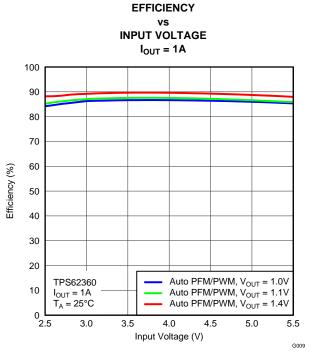
Figure 8.





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### TYPICAL CHARACTERISTICS (continued)

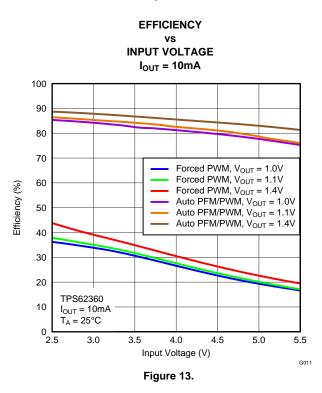


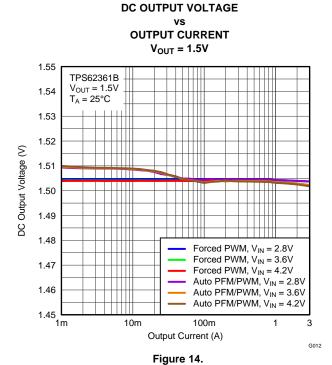
**INPUT VOLTAGE**  $I_{OUT} = 100mA$ 100 90 80 70 60 Efficiency (%) 50 40 30 Forced PWM,  $V_{OUT} = 1.0V$ Forced PWM, V<sub>OUT</sub> = 1.1V 20 Forced PWM, V<sub>OUT</sub> = 1.4V Auto PFM/PWM, V<sub>OUT</sub> = 1.0V TPS62360 10 Auto PFM/PWM, V<sub>OUT</sub> = 1.1V  $I_{OUT} = 100 \text{mA}$  $T_A = 25^{\circ}C$ Auto PFM/PWM, V<sub>OUT</sub> = 1.4V 0 **L** 2.5 3.0 4.0 4.5 5.0 3.5 5.5 Input Voltage (V) G010

**EFFICIENCY** 

Figure 11.

Figure 12.







### TYPICAL CHARACTERISTICS (continued)

G013

### DC OUTPUT VOLTAGE **OUTPUT CURRENT** $V_{OUT} = 1.2V$ 1.25 TPS62361B $V_{OUT} = 1.2V$ 1.24 $T_A = 25^{\circ}C$ 1.23 1.22 DC Output Voltage (V) 1.21 1.20 1.19 1.18 Forced PWM, V<sub>IN</sub> = 2.8V Forced PWM, V<sub>IN</sub> = 3.6V Forced PWM, V<sub>IN</sub> = 4.2V 1.17 Auto PFM/PWM, V<sub>IN</sub> = 2.8V 1.16 Auto PFM/PWM, $V_{IN} = 3.6V$ Auto PFM/PWM, $V_{IN} = 4.2V$ 1.15 100m 1m 10m Output Current (A)

DC OUTPUT VOLTAGE vs OUTPUT CURRENT V<sub>OUT</sub> = 0.9V

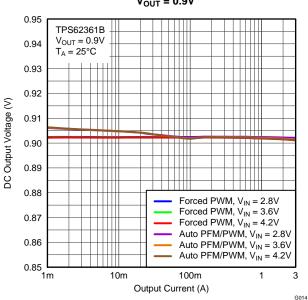


Figure 16.

Figure 15.

# DC OUTPUT VOLTAGE vs OUTPUT CURRENT $V_{OUT} = 0.6V$

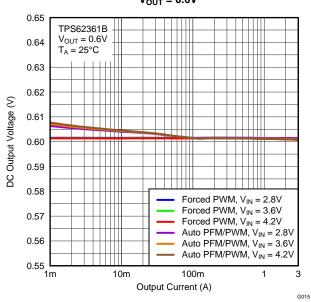


Figure 17.

# STARTUP INTO NO LOAD $V_{OUT} = 0.5V$

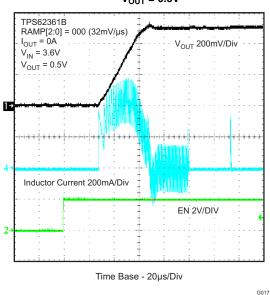


Figure 18.

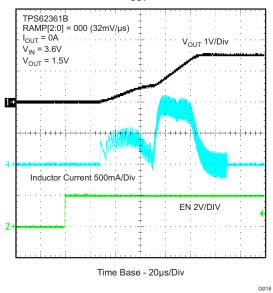
G019

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### TYPICAL CHARACTERISTICS (continued)

### STARTUP INTO NO LOAD

### STARTUP INTO LOAD $V_{OUT} = 1.5V$ $V_{OUT} = 0.5V$



TPS62361B RAMP[2:0] = 000 (32mV/µs) I<sub>OUT</sub> = 1A V<sub>OUT</sub> 200mV/Div V<sub>IN</sub> = 3.6V  $V_{OUT} = 0.5V$ 15 Inductor Current 500mA/Div EN 2V/DIV

Figure 19.

Figure 20.

Time Base - 20µs/Div

### STARTUP INTO LOAD $V_{OUT} = 1.5V$

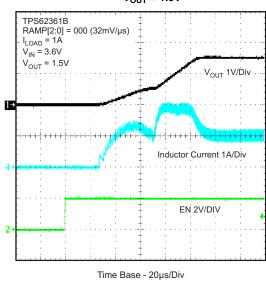
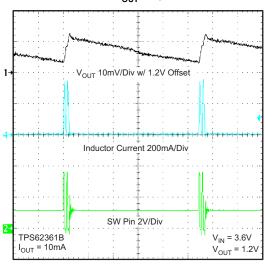


Figure 21.

### **SWITCHING WAVE FORMS** $I_{OUT} = 10mA$



Time Base - 4µs/Div

Figure 22.



### TYPICAL CHARACTERISTICS (continued)

G022

# SWITCHING WAVE FORMS I<sub>OUT</sub> = 200mA

# TPS62361B I<sub>OUT</sub> = 200mA V<sub>IN</sub> = 3.6V V<sub>OUT</sub> = 1.2V V<sub>OUT</sub> 10mV/Div w/ 1.2V Offset Inductor Current 200mA/Div w/ 200mA Offset

Figure 23.

Time Base - 250ns/Div

# SWITCHING WAVE FORMS I<sub>OUT</sub> = 1A

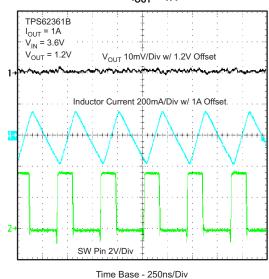


Figure 24.

G023

# SWITCHING WAVE FORMS

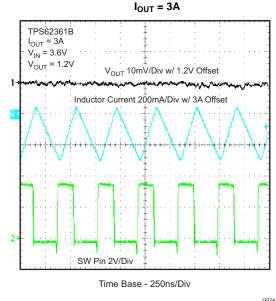


Figure 25.

# OUTPUT VOLTAGE RAMP CONTROL NO LOAD

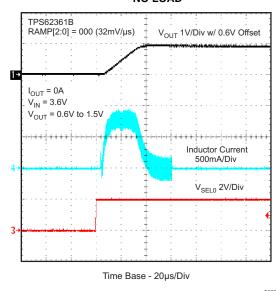


Figure 26.

### TYPICAL CHARACTERISTICS (continued)

G026

### **OUTPUT VOLTAGE RAMP CONTROL**

# $I_{OUT} = 1A$

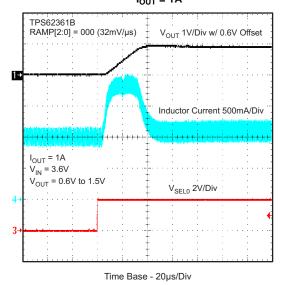


Figure 27.

### LOAD TRANSIENT RESPONSE I<sub>OUT</sub> RANGE: 5mA to 200mA

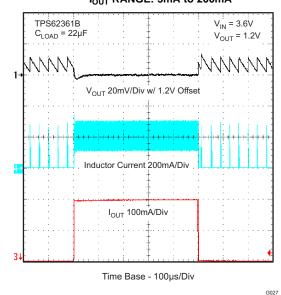


Figure 28.

### LOAD TRANSIENT RESPONSE I<sub>OUT</sub> RANGE: 5mA to 1A

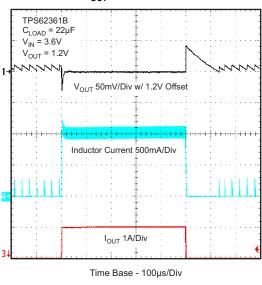


Figure 29.

### LOAD TRANSIENT RESPONSE I<sub>OUT</sub> RANGE: 200mA to 1A

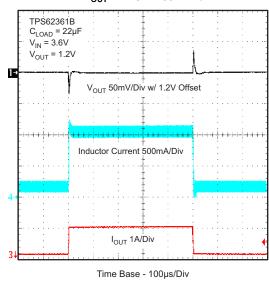
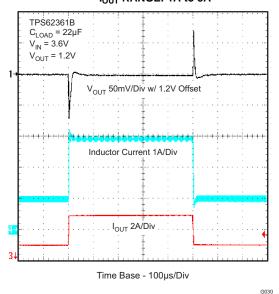


Figure 30.



### TYPICAL CHARACTERISTICS (continued)

### LOAD TRANSIENT RESPONSE I<sub>OUT</sub> RANGE: 1A to 3A



LINE TRANSIENT RESPONSE VIN RANGE: 4.2V to 3.2V

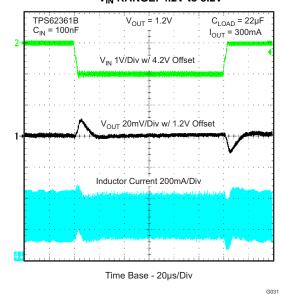


Figure 31.

**SHUTDOWN CURRENT** 

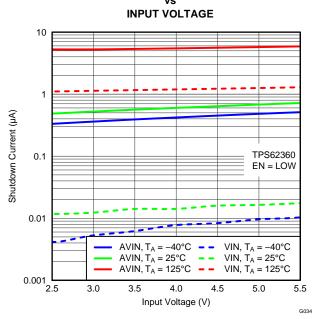


Figure 33.

Figure 32.

## **QUIESCENT CURRENT INPUT VOLTAGE**

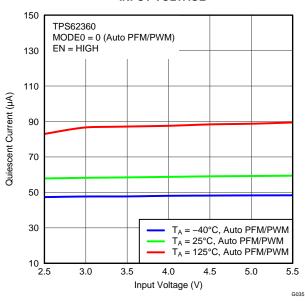
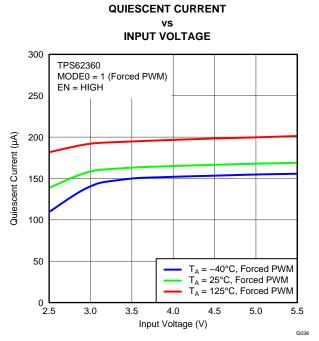


Figure 34.

### TYPICAL CHARACTERISTICS (continued)



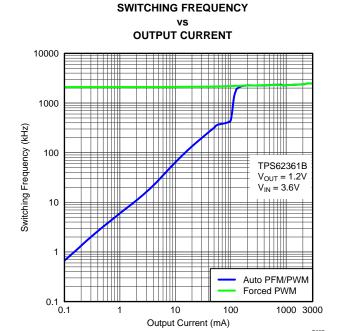
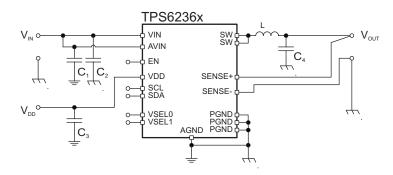


Figure 35. Figure 36.

### **FET CURRENT LIMIT INPUT VOLTAGE** 4.0 3.8 3.6 3.4 FET Current Limit (A) 3.2 3.0 2.8 2.6 2.4 High Side PMOS Current Limit 2.2 TPS62360 Low Side NMOS Current Limit $T_A = 25^{\circ}C$ Negative NMOS Current Limit 2.0 - 2.5 4.0 4.5 3.0 3.5 5.5 Input Voltage (V) Figure 37.



### PARAMETER MEASUREMENT INFORMATION



**Table 1. List of Components** 

REFERENCE	DESCRIPTION	MANUFACTURER
TPS6236x	TPS62360 / TPS62361B / TPS62362	Texas Instruments
L	1 μH, 4 mm x 4 mm x 2.1 mm	Coilcraft (XFL4020-102ME1.0)
C <sub>2</sub> , C <sub>4</sub>	10 μF, Ceramic, 6.3V, X5R	Murata (GRM188R60J106ME84D)
C <sub>1</sub> , C <sub>3</sub>	0.1 μF, Ceramic, 10V, X5R	Standard



### DETAILED DESCRIPTION

The TPS6236x are a family of high-frequency synchronous step down dc-dc converter optimized for battery-powered portable applications. With an input voltage range of 2.5V to 5.5V, common battery technologies are supported.

The device provides up to 3A peak load current, operating at 2.5MHz typical switching frequency.

The devices convert to an output voltage range of 0.77V to 1.4V (TPS62360 / TPS62362) and 0.5V to 1.77V (TPS62361B), programmable via I<sup>2</sup>C interface in 10mV steps.

The TPS6236x supports low-voltage DSPs and processor cores in smart-phones and handheld computers, including latest submicron processes and their retention modes and addresses digital voltage scaling technologies such as SmartReflex™.

Output Voltages and Modes can be fully programmed via I<sup>2</sup>C. To address different performance operating points and/or startup conditions, the device offers four output voltage / mode presets which can be chosen via dedicated hardware input pins allowing simple and zero latency output voltage transition.

The devices focus on a high output voltage accuracy. The fully differential sensing and the DCS-Control™ architecture achieve precise static and dynamic, transient output voltage regulation. This accounts for stable processor operation. Output voltage security margins can be kept small, resulting in an increased overall system efficiency.

The TPS6236x devices offer high efficiency step down conversion. The area of highest efficiency is extended towards low output currents to increase the efficiency while the processor is operating in retention mode, as well as towards highest output currents reducing the power loss. This addresses the power profile of processors. High efficiency conversion is required for low output currents to support the retention modes of processors, resulting in an increased battery on-time. To address the processor maximum performance operating points with highest output currents, high efficiency conversion is enabled as well to save the battery on-time and reduce input power.

The robust architecture and multiple safety features allow perfect system integration.

The 2mm x 2mm package and the low number of required external components lead to a tiny solution size of approximately 27.5 mm<sup>2</sup>.

### **OPERATION**

The TPS6236x synchronous switched mode power converters are based on DCS-Control™, an advanced regulation topology, that combines the advantages of hysteretic, voltage mode and current mode control architectures.

While a comparator stage provides excellent load transient response, an additional voltage loop ensures high DC accuracy as well. The TPS6236x compensates ground shifts at the load by the differentially sensing the output voltage at the point of load.

The internal ramp generator adds information about the load current and fast output voltage changes. The internally compensated regulation network achieves fast and stable operation with low ESR capacitors.

The DCS-Control™ topology supports PWM (Pulse Width Modulation) mode for medium and heavy load conditions and a Power Save Mode at light loads. During PWM it operates at its nominal switching frequency in continuous conduction mode. This frequency is typically about 2.5MHz with a controlled frequency variation depending on the input voltage. As the load current decreases, the converter enters Power Save Mode to sustain high efficiency down to light loads. The transition from PWM to Power Save Mode is seamless and avoids output voltage transients.

An internal current limit supports nominal output currents of up to 3A. The TPS6236x family offers both excellent DC voltage and superior load transient regulation, combined with very low output voltage ripple, minimizing interference with RF circuits.

### **ENABLING AND DISABLING THE DEVICE**

The device is enabled by setting the EN input to a logic high. Accordingly, a logic low disables the device. If the device is enabled, the internal power stage will start switching and regulate the output voltage to the programmed threshold. The EN input must be terminated unless the internal pull down resistor is activated.

20



The I<sup>2</sup>C interface is operable when VDD and AVIN are present, regardless of the state of the EN pin.

If the device is disabled by pulling the EN to a logic low, the output capacitor can actively be discharged. Per default, this feature is disabled. Programming the EN\_DISC bit to a logic high will discharge the output capacitor via a typ.  $300\Omega$  path on the SENSE+ pin.

### **SOFT START**

The device incorporates an internal soft start circuitry that controls the ramp up of the output voltage after enabling the device. This circuitry eliminates inrush current to avoid excessive voltage drops of primary cells and rechargeable batteries with high internal impedance.

During soft start, the output voltage is monotonically ramped up to the minimum programmable output voltage. After reaching this threshold, the output voltage is further increased following the slope as programmed in the ramp rate settings (see RAMP RATE CONTROLLING) until reaching the programmed output voltage. Once the nominal voltage is reached, regular operation as described above will continue.

The device is able to start into a pre biased output capacitor as well.

### PROGRAMMING THE OUTPUT

The TPS6236x devices offer four similar registers to program the output. Two dedicated hardware input pins, VSEL0 and VSEL1, are implemented for choosing the active register. The logic state of VSEL0 and VSEL1 select the register whose settings are present at the output. The VSEL0 and VSEL1 pins must be terminated unless the internal pull-down resistors are activated.

The registers have a certain initial default value (see Table 2) and can be readjusted via I<sup>2</sup>C during operation.

This allows a simple transition between several output options by triggering the dedicated input pins. At the same time since the presets can be readjusted during operation, this offers highest flexibility.

INPU	T PINS	DDECET	I <sup>2</sup> C REGISTER	DEFAULT OPERATION MODE	DEFAUL	T OUTPUT VOL	TAGE [V]
VSEL1	VSEL0	PRESET	FC REGISTER	TPS62360, TPS62361B, TPS62362	TPS62360	TPS62361B	TPS62362
0	0	SET0	0x00h – see Table 12, Table 13 and Table 14	Power Save Mode	1.40	0.96	1.23
0	1	SET1	0x01h – see Table 15, Table 16 and Table 17	Power Save Mode	1.00	1.40	1.00
1	0	SET2	0x02h – see Table 18, Table 19 and Table 20	Power Save Mode	1.40	1.16	1.20
1	1	SET3	0x03h – see Table 21, Table 22 and Table 23	Power Save Mode	1.10	1.16	1.10

**Table 2. Output Presets** 

Via the I<sup>2</sup>C interface and/or the four preset options, the following output parameters can be changed:

- Output voltage from 0.77 V to 1.4 V (TPS62360/62) and 0.5V to 1.77V (TPS62361B) with 10 mV granularity
- Mode of operation: Power Save Mode or forced PWM mode

The slope for transition between different output voltages (Ramp Rate) can be changed via I<sup>2</sup>C as well. The slope applies for all presets globally. See RAMP RATE CONTROLLING for further details.

Since the output parameters can be changed by dedicated pins for selecting presets and by I<sup>2</sup>C, the following use scenarios are feasible:

- Control the device via dedicated pins only, after programming the presets, to choose and change within the programmed settings
- Program via I<sup>2</sup>C only. The dedicated input pins have fixed connections. Changes are conducted by changing the preset values of the active register.
- Dedicated input pins and I<sup>2</sup>C mixed operation. The non active presets might be changed. The dedicated input pins are used for the transition to the new output condition. Changes within an active preset via I<sup>2</sup>C are feasible as well.

### DYNAMIC VOLTAGE SCALING

The output voltage can be adjusted dynamically. Each of the four output registers can be programmed individually by setting OV[5:0] (TPS62360/62) and OV[6:0] (TPS62361B) respectively in the SET0, SET1, SET2 and SET3 registers.

Table 3. TPS62360, TPS62362 Output Voltage Settings for Registers SET0, SET1, SET2 and SET3

REGISTERS: SET0, SET1, SET2, SET3				
OV[D5:D0]	OUTPUT VOLTAGE			
00 0000	770 mV			
00 0001	780 mV			
00 0010	790 mV			
00 0011	800 mV			
11 1101	1380 mV			
11 1110	1390 mV			
11 1111	1400 mV			

Table 4. TPS62361B Output Voltage Settings for Registers SET0, SET1, SET2 and SET3

REGISTERS: SET0, SET1, SET2, SET3							
OV[D6:D0]	OUTPUT VOLTAGE						
000 0000	500 mV						
000 0001	510 mV						
000 0010	520 mV						
000 0011	530 mV						
111 1101	1750 mV						
111 1110	1760 mV						
111 1111	1770 mV						

If the output voltage is changed at the active register (selected by VSEL0 and VSEL1), these changes will apply after the I<sup>2</sup>C command is sent.

### POWER SAVE MODE AND FORCED PWM MODE

The TPS6236x devices feature a Power Save Mode to gain efficiency at light output current conditions. The device automatically transitions in both directions between pulse width modulation (PWM) operation at high load and pulse frequency modulation (PFM) operation at light load current. This maintains high efficiency at both light and heavy load currents. In PFM Mode, the device generates single switching pulses when required to maintain the programmed output voltage.

The transition into and out of Power Save Mode happens within the entire regulation scheme and is seamless in both directions.

The output current, at which the device transitions from PWM to PFM operation can be estimated as follows:

$$I_{\text{OUT,TRANS}} = \frac{V_{\text{IN}} - V_{\text{OUT}}}{2} \times \frac{V_{\text{OUT}}}{V_{\text{IN}}} \times \frac{1}{(f \times L)}$$
(1)

With:

V<sub>IN</sub> = Input voltage V<sub>OUT</sub> = Output Voltage

f = Switching frequency, typ. 2.5 MHz

L = Inductor value



The TPS6236x is optimized for low output voltage ripple. Therefore, the peak inductor current in PFM mode is kept small and can be calculated as follows:

$$I_{L,PFM,peak} = \frac{t_{ON}}{L} \times (V_{IN} - V_{OUT})$$
(2)

And:

$$t_{ON} = \frac{V_{OUT}}{V_{IN}} \times 350ns + 20ns \tag{3}$$

With:

V<sub>IN</sub> = Input Voltage

V<sub>OUT</sub> = Output Voltage

t<sub>ON</sub> = On-time of the High Side FET, from Equation 3

L = Inductor value

The TPS6236x offers a forced PWM mode as well. In this mode, the converter is forced in PWM mode even at light load currents. This comes with the benefit that the converter is operating with lower output voltage ripple. Compared to the PFM mode, the efficiency is lower during light load currents.

According to the output voltage, the Power Save Mode / forced PWM Mode can be programmed individually for each preset via  $I^2C$  by setting the MODE0 – MODE3 bit D7. Table 2 shows the factory presets after enabling the  $I^2C$ . For additional flexibility, the Power Save Mode can be changed at a preset that is currently active.

### RAMP RATE CONTROLLING

If the output voltage is changed, the TPS6236x can actively control the voltage ramp rate during the transition. An internal oscillator is embedded for high timing precision.

Figure 38 and Figure 39 show the operation principle. If the output voltage changes, the device will change the output voltage through discrete steps with a programmable ramp rate resulting in a corresponding transition time.

The ramp up/down slope can be programmed via I<sup>2</sup>C interface (see Table 5).

RAMP RATE RMP [2:0] [mV/µs] [µs/10mV] 000 32 0.3125 001 16 0.625 1.25 010 8 011 4 2.5 100 2 5 101 1 10 110 0.5 20 111 0.25

Table 5. Ramp Rates

For a transition of the output voltage from  $V_{\text{OUT,A}}$  to  $V_{\text{OUT,B}}$  and vice versa, the resulting ramp up/down slope can be calculated as

$$\frac{\Delta V_{OUT}}{\Delta t} = 32 \frac{mV}{\mu s} \frac{1}{2^{(RMP[2-0])_2}}$$
 (4)

If the device is operating in forced PWM Mode, the device actively controls both the ramp up and down slope.

If Power Save Mode is activated, the ramp up phase follows the programmed slope.

To force the output voltage to follow the ramp down slope in Power Save Mode, the RAMP\_PFM bit needs to be set. This will force the converter to follow the ramp down slope during PFM operation as well.

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If the RAMP\_PFM bit is not set in Power Save Mode, the slope can be less at low output currents since the device does not actively source energy back from the output capacitor to the input or it might be sharper at high output currents since the output capacitor is discharged quickly.

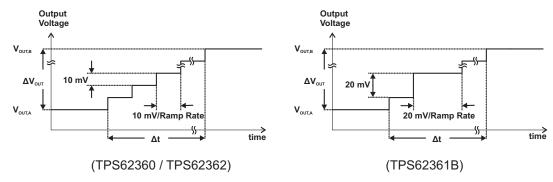


Figure 38. Ramp Up

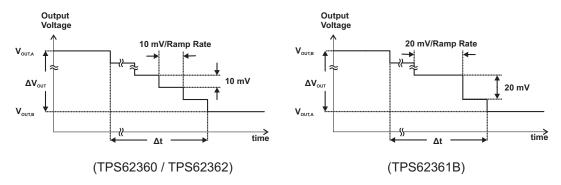


Figure 39. Ramp Down

The TPS62360 and TPS62362 ramp the output voltage taking 10mV steps, while the TPS62361B ramps taking 20mV steps with a final 10mV step if required. The resulting slope remains equal for both devices.

While the output voltage setpoint is changed in a digital stair step fashion, the output voltage change will be linear due to the output capacitor whose voltage cannot change instantaneously.

### SAFE OPERATION AND PROTECTION FEATURES

### **Inductor Current Limit**

The inductor current limiting prevents the device from drawing high inductor current and excessive current from the battery. Excessive current might occur with a shorted/saturated inductor or a heavy load/shorted output circuit condition.

The incorporated inductor peak current limit measures the current while the high side power MOSFET is turned on. Once the current limit is tripped, the high side MOSFET is turned off and the low side MOSFET is turned on to ramp down the inductor current. This prevents high currents to be drawn from the battery.

Once the low side MOSFET is on, the low side forward current limit keeps the low side MOSFET on until the current through it decreases below the low side forward current limit threshold.

The negative current limit acts if current is flowing back to the battery from the output. It works differently in PWM and PFM operation. In PWM operation, the negative current limit prevents excessive current from flowing back through the inductor to the battery, preventing abnormal voltage conditions at the switching node. In PFM operation, a zero current limits any power flow back to the battery by preventing negative inductor current.

### Die Temperature Monitoring and Over Temperature Protection

The TPS6236x offers two stages of die temperature monitoring and protection.



The Early Warning Monitoring Feature monitors the device temperature and provides the host an indication that the die temperature is in the higher range. If the device's junction temperature, T<sub>J</sub>, exceeds 120°C typical, the TJEW bit is set high. To avoid the thermal shutdown being triggered, the current drawn from the TPS6236x should be reduced at this early stage.

The Over Temperature Protection feature disables the device if the temperature increases due to heavy load and/or high ambient temperature. It monitors the device die temperature and, if required, triggers the device into shutdown until the die temperature falls sufficiently.

If the junction temperature,  $T_J$ , exceeds 150°C typical, the device goes into thermal shutdown. In this mode, the power stage is turned off. During thermal shutdown, the  $I^2C$  interface remains operable. All register values are kept.

For the thermal shutdown, a hysteresis of  $20^{\circ}$ C typical is implemented allowing the device to cool after the shutdown is triggered. Once the junction temperature  $T_J$  cools down to  $130^{\circ}$ C typical, the device resumes operation.

If a thermal shutdown has occurred, the TJTS bit is latched and remains a logic high as long as VDD and AVIN are present and until the bit is reset by the host.

### Input Under Voltage Protection

The input under voltage protection is implemented in order to prevent operation of the device for low input voltage conditions. If the device is enabled, it prevents the device from switching if AVIN falls below the under voltage lockout threshold. If the AVIN under voltage protection threshold is tripped, the device will go into under voltage shutdown instantaneously, turning the power stage off and resetting all internal registers. The input under voltage protection is also implemented on the VDD input. If the VDD under voltage protection threshold is tripped, the device will reset all internal registers.

A under voltage lockout hysteresis of V<sub>UVLO.HYST(AVIN)</sub> at AVIN and V<sub>UVLO.HYST(VDD)</sub> at VDD is implemented.

The I<sup>2</sup>C compatible interface remains fully functional if AVIN and VDD are present. If the under voltage lockout of AVIN or VDD is triggered during operation, all internal registers are reset to their default values. Figure 40 shows the UVLO block diagram.

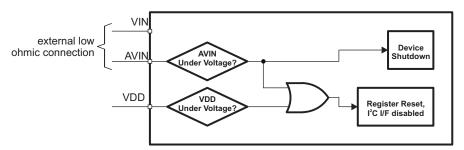


Figure 40. UVLO State Chart

By connecting VIN and AVIN to the same potential, VIN is included in the under voltage monitoring. If a low pass input filter is applied at AVIN (not mandatory for the TPS6236x), the delay and shift in the voltage level can be calculated by taking the typical quiescent current  $I_Q$  at AVIN. As an example, for  $I_Q$  and  $10\Omega$  series resistance, this results in a minimal static shift of approx.  $560\mu$ V.

VIN and AVIN must be connected to the same source for proper device operation.

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### **APPLICATION INFORMATION**

### I<sup>2</sup>C INTERFACE

### **Serial Interface Description**

I<sup>2</sup>C is a 2-wire serial interface developed by Philips Semiconductor (see I<sup>2</sup>C-Bus Specification, Version 2.1, January 2000). The bus consists of a data line (SDA) and a clock line (SCL) with pull-up structures. When the bus is *idle*, both SDA and SCL lines are pulled high. All the I<sup>2</sup>C compatible devices connect to the I<sup>2</sup>C bus through open drain I/O pins, SDA and SCL. A *master* device, usually a micro controller or a digital signal processor, controls the bus. The master is responsible for generating the SCL signal and device addresses. The master also generates specific conditions that indicate the START and STOP of data transfer. A *slave* device receives and/or transmits data on the bus under control of the master device.

The TPS6236x device works as a *slave* and supports the following data transfer *modes*, as defined in the  $I^2C$ -Bus Specification:

- Standard mode (100 kbps)
- Fast mode (400 kbps)
- · Fast mode plus (1Mbps)
- High-speed mode (3.4 Mbps)

The interface adds flexibility to the power supply solution, enabling most functions to be programmed to new values depending on the instantaneous application requirements. Register contents remain intact as long as VDD and AVIN are present in the specified range. Tripping the under voltage lockout of AVIN or VDD deletes the registers and establishes the default values once the supply is present again.

The data transfer protocol for standard and fast modes is exactly the same; therefore, they are referred to as F/S-mode in this document. The protocol for high-speed mode is different from F/S-mode, and it is referred to as HS-mode. The TPS6236x device supports 7-bit addressing. 10-bit addressing and general call addressing are not supported.

Table 6 shows the TPS6236x devices and their assigned I<sup>2</sup>C addresses.

 I²C ADDRESS

 HEXADECIMAL CODED
 BINARY CODED

 TPS62360
 (0x60)<sub>HEX</sub>
 (110 0000)<sub>2</sub>

 TPS62361B
 (0x60)<sub>HEX</sub>
 (110 0000)<sub>2</sub>

 TPS62362
 (0x60)<sub>HEX</sub>
 (110 0000)<sub>2</sub>

Table 6. I<sup>2</sup>C Address

### F/S-Mode Protocol

The master initiates data transfer by generating a start condition. The start condition is when a high-to-low transition occurs on the SDA line while SCL is high, as shown in Figure 41. All I<sup>2</sup>C-compatible devices should recognize a start condition.

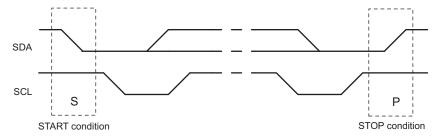


Figure 41. START and STOP Conditions

The master then generates the SCL pulses, and transmits the 7-bit address and the read/write direction bit R/W on the SDA line. During all transmissions, the master ensures that data is valid. A valid data condition requires



the SDA line to be stable during the entire high period of the clock pulse (see Figure 42). All devices recognize the address sent by the master and compare it to their internal fixed addresses. Only the slave device with a matching address generates an acknowledge (see Figure 43) by pulling the SDA line low during the entire high period of the ninth SCL cycle. Upon detecting this acknowledge, the master knows that communication link with a slave has been established.

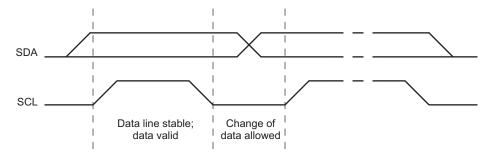


Figure 42. Bit Transfer on the Serial Interface

The master generates further SCL cycles to either transmit data to the slave (R/W bit 1) or receive data from the slave (R/W bit 0). In either case, the receiver needs to acknowledge the data sent by the transmitter. So an acknowledge signal can either be generated by the master or by the slave, depending on which one is the receiver. 9-bit valid data sequences consisting of 8-bit data and 1-bit acknowledge can continue as long as necessary.

To signal the end of the data transfer, the master generates a stop condition by pulling the SDA line from low to high while the SCL line is high (see Figure 41). This releases the bus and stops the communication link with the addressed slave. All I<sup>2</sup>C compatible devices must recognize the stop condition. Upon the receipt of a stop condition, all devices know that the bus is released, and they wait for a start condition followed by a matching address.

Attempting to read data from register addresses not listed in this section will result in 00h being read out.

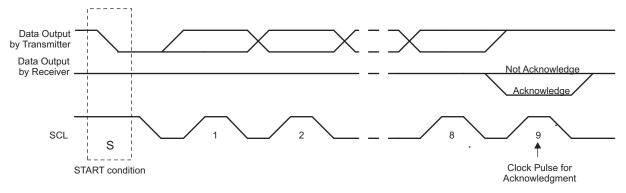


Figure 43. Acknowledge on the I<sup>2</sup>C Bus

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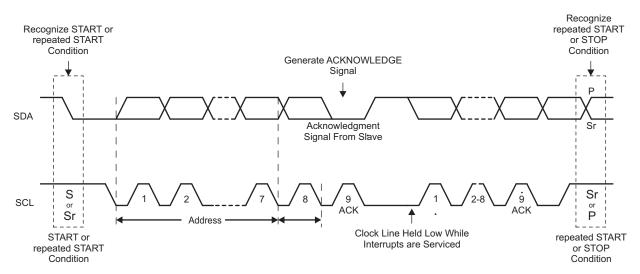


Figure 44. Bus Protocol

### **HS-Mode Protocol**

When the bus is idle, both SDA and SCL lines are pulled high by the pull-up devices.

The master generates a start condition followed by a valid serial byte containing HS master code 00001XXX. This transmission is made in F/S-mode at no more than 400 Kbps. No device is allowed to acknowledge the HS master code, but all devices must recognize it and switch their internal setting to support 3.4 Mbps operation.

The master then generates a *repeated start condition* (a repeated start condition has the same timing as the start condition). After this repeated start condition, the protocol is the same as F/S-mode, except that transmission speeds up to 3.4 Mbps are allowed. A stop condition ends the HS-mode and switches all the internal settings of the slave devices to support the F/S-mode. Instead of using a stop condition, repeated start conditions should be used to secure the bus in HS-mode.

Attempting to read data from register addresses not listed in this section will result in 00h being read out.

### I<sup>2</sup>C UPDATE SEQUENCE

The TPS6236x requires a start condition, a valid I<sup>2</sup>C address, a register address byte, and a data byte for a single update. After the receipt of each byte, the TPS6236x device acknowledges by pulling the SDA line low during the high period of a single clock pulse. A valid I<sup>2</sup>C address selects the TPS6236x. The TPS6236x performs an update on the falling edge of the acknowledge signal that follows the LSB byte.

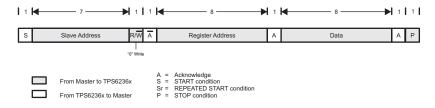


Figure 45. Write Data Transfer Format in F/S-Mode



Figure 46. Read Data Transfer Format in F/S-Mode

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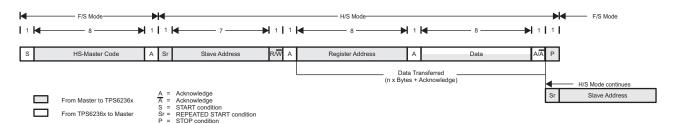


Figure 47. Data Transfer Format in H/S-Mode

### **Slave Address Byte**

MSB							LSB
X	X	X	X	X	X	A1	A0

The slave address byte is the first byte received following the START condition from the master device.

### **Register Address Byte**

MSB							LSB
0	0	0	0	0	D2	D1	D0

Following the successful acknowledgment of the slave address, the bus master will send a byte to the TPS6236x, which will contain the address of the register to be accessed.

### I<sup>2</sup>C REGISTER RESET

The I<sup>2</sup>C registers can be reset by pulling VDD to GND. Refer to the Input Under Voltage Protection section for details.

### **PULL DOWN RESISTORS**

The EN, VSEL0 and VSEL1 inputs feature internal pull down resistors to discharge the potential if one of the pins is not connected or is triggered by a high impedance source.

To achieve lowest possible quiescent current, the pull down resistors can be disabled individually at EN, VSEL0 and VSEL1 by I<sup>2</sup>C programming the registers PD\_EN, PD\_VSEL0 and PD\_VSEL1.

By default, the pull down resistors are enabled.

### INPUT CAPACITOR SELECTION

The input capacitor is required to buffer the pulsing current drawn by the device at VIN and reducing the input voltage ripple. The pulsing current is originated by the operation principles of a step down converter.

Low ESR input capacitors are required for best input voltage filtering and minimal interference with other system components. For best performance, ceramic capacitors with a low ESR at the switching frequency are recommended. X7R or X5R type capacitors should be used.

A ceramic input capacitor in the nominal range of  $C_{IN} = 4.7 \mu F$  to  $22 \mu F$  should be a good choice for most application scenarios. In general, there is no upper limit for increasing the input capacitor.

For typical operation, a  $10\mu F$  X5R type capacitor is recommended. Table 7shows a list of recommended capacitors.

**Table 7. List of Recommended Capacitors** 

CAPACITANCE [µF]	TYPE	DIMENSIONS L x W x H [mm³]	MANUFACTURER
10	GRM188R60J106M	0603: 1.6 x 0.8 x 0.8	Murata
10	CL10A106MQ8NRNC	0603: 1.6 x 0.8 x 0.8	Samsung

CAPACITANCE [µF]	TYPE	DIMENSIONS L x W x H [mm³]	MANUFACTURER
22	GRM188R60G226M	0603: 1.6 x 0.8 x 0.8	Murata
22	CL10A106MQ8NRNC	0603: 1.6 x 0.8 x 0.8	Samsung

### **DECOUPLING CAPACITORS AT AVIN, VDD**

Noise impacts can be reduced by buffering AVIN and VDD with a decoupling capacitor. It is recommended to buffer AVIN and VDD with a X5R or X7R ceramic capacitor of at least  $0.1\mu F$  connected between AVIN, AGND and VDD, AGND respectively. The capacitor closest to the pin should be kept small (<  $0.22\mu F$ ) in order to keep a low impedance at high frequencies. In general, there is no upper limit for the total capacitance.

### INDUCTOR SELECTION

The choice of the inductor type and value has an impact on the inductor ripple current, the transition point of PFM to PWM operation, the output voltage ripple and accuracy. The subsections below support for choosing the proper inductor.

### **Inductance Value**

The TPS6236x is designed for best operation with a nominal inductance value of 1µH.

Choosing a smaller value than 1µH improves the load transient behavior, whereas choosing a higher value reduces the ripple current resulting in a smaller output voltage ripple and better DC output regulation. The inductor current ripple can be calculated as:

$$\Delta I_{L} = V_{OUT} \times \frac{1 - \frac{V_{OUT}}{V_{IN}}}{L \times f}$$
(5)

With:

V<sub>IN</sub> = Input Voltage

V<sub>OUT</sub> = Output Voltage

f =Switching frequency, typ. 2.5 MHz

L = Inductor value

### **Inductor Saturation Current**

The inductor needs to be selected for its current rating. To pick the proper saturation current rating, the maximum inductor current can be calculated as:

$$I_{L,MAX} = I_{OUT,MAX} + \frac{\Delta I_L}{2}$$
(6)

With:

 $\Delta I_L$  = Inductor ripple current (see Equation 5)

 $I_{OUT,MAX} = Maximum output current$ 

Since the inductance can be decreased by saturation effects and temperature impact, the inductor needs to be chosen to have an effective inductance of at least 0.6µH under temperature and saturation effects.

### Table 8. List of Recommended Inductors

INDUCTANCE [µH]	SATURATION CURRENT RATING (30% inductance drop, typ) [A]	DIMENSIONS L x W x H [mm³]	DC RESISTANCE [mΩ typ]	ТҮРЕ	MANUFACTURER
1.0	3.4	3.2 x 2.5 x 1.2	51	PST032251B-1R0MS-11	Cyntec
1.0	2.5	3.2 x 2.5 x 1.0	55	KSLI-322510BL1-1R0	Hitachi Metals
1.0	5.4	4 x 4 x 2.1	10	XFL4020-102ME1.0	Coilcraft



### Table 8. List of Recommended Inductors (continued)

INDUCTANCE [µH]	SATURATION CURRENT RATING (30% inductance drop, typ) [A]	DIMENSIONS L x W x H [mm³]	DC RESISTANCE [mΩ typ]	ТҮРЕ	MANUFACTURER
1.0	5.4	3.2 x 3 x 1.2	57	SPM3012T-1R0M	TDK
1.0	2.7	3 x 2.8 x 1.5	27	DEM2815C 1226AS-H-1R0N	Toko

### **OUTPUT CAPACITOR SELECTION**

The unique hysteretic control scheme allows the use of tiny ceramic capacitors. For best performance, ceramic capacitors with low ESR values are recommended to achieve high conversion efficiency and low output voltage ripple. For stable operation, X7R or X5R type capacitors are recommended.

The TPS6236x is designed to operate with an output capacitor of  $10\mu\text{F}$  to  $22\mu\text{F}$ , placed at the device's output. In addition a  $0.1\mu\text{F}$  capacitor can be added to the output to reduce the high frequency content created by a very sudden load change.

At light loads, if the device is operating in PFM Mode, choosing a higher value will minimize the voltage ripple resulting in a better DC output accuracy.

Buffering the processor input by an additional ceramic capacitor in the range of  $10\mu\text{F}$  to  $22\mu\text{F}$  improves the voltage quality at the processor input and the dynamic load step behavior. This is especially true if the trace between the TPS6236x and the microprocessor is longer than the smallest possible. This additional capacitor needs to be taken into account for the recommended capacitance value. For stability, the sum of the VOUT capacitors should not exceed  $75\mu\text{F}$  effective capacitance.

Table 7 shows a list of tested capacitors. The TPS6236x is not designed for use with polymer, tantalum, or electrolytic output capacitors.

### **OUTPUT FILTER DESIGN**

The inductor and the output capacitor build the output filter. The load might be buffered with an input capacitor  $C_{LOAD}$ , which needs to be factored in. Based on the output capacitor and inductance recommendation sections and factoring in  $C_{LOAD}$ , these components should be in the range:

- $C_{OUT} + C_{LOAD} = 10\mu F$  to  $75\mu F$
- L = 1 uH

For further performance or specific demands, these values might be tweaked. In any case, the loop stability should be checked since the control loop stability might be affected.

### THERMAL AND DEVICE LIFE TIME INFORMATION

Implementation of integrated circuits in low-profile and fine-pitch surface-mount packages typically requires special attention to power dissipation. Many system-dependent issues such as thermal coupling, airflow, added heat sinks and convection surfaces, and the presence of other heat-generating components affect the power-dissipation limits of a given component.

Thermal performance can be enhanced by proper PCB layout. Wide power traces come with the ability to sink dissipated heat. This can be improved further on multi layer PCB designs with vias to different layers.

Proper PCB layout with focus on thermal performance results in a reduced junction-to-ambient thermal resistance  $\theta_{JA}$  and thereby reduces the device junction temperature,  $T_{J}$ .

The TI reliability requirement for the silicon chip's life time (100K Power-On-Hours at  $T_J = 105^{\circ}\text{C}$ ) is affected by the junction temperature and the continuously drawn current at the VIN pin and the SW pins. In order to be consistent with the TI reliability requirement for the silicon chips (100000 Power-On-Hours at  $T_J = 105^{\circ}\text{C}$ ), the VIN pin current should not continuously exceed 1275mA and the SW pins current should not continuously exceed 2550mA so as to prevent electromigration failure in the solder bump. Drawing 1150mA at VIN would, as an example, be the case for typically  $I_{OUT} = 2350$ mA,  $V_{OUT} = 1.5$ V and  $V_{IN} = 3.6$ V.



Exceeding the VIN pin / SW pins current rating might affect the device reliability. As an example, drawing current peaks  $I_{OUT} = 3000$ mA with up to 10% of the application time over a base continuous output current  $I_{OUT} = 2000$ mA might reduce the Power-on-Hours to 90000 hours for conditions such as  $V_{IN} = 2.7V$ ,  $V_{OUT} = 1.5V$ ,  $V_{OUT} = 1$ 

For more details on how to use the thermal parameters, see the application notes: Thermal Characteristics Application Note (SZZA017), and IC Package Thermal Metrics Application Note (SPRA953).

### PCB LAYOUT CONSIDERATIONS

The PCB layout is an important step to maintain the high performance of the TPS6236x. Both the high current and the fast switching nodes demands full attention to the PCB layout.

The input / output capacitors and the inductor should be placed as close as possible to the IC. This keeps the traces short. Routing these traces direct and wide results in low trace resistance and low parasitic inductance. A common power GND should be used. The low side of the input and output capacitors must be connected to the power GND, as well as the PGND node. AGND and PGND should be connected close to the IC but at a single place.

The sense traces connected to SENSE+ and SENSE- are signal traces. Special care should be taken to avoid noise being induced. By a direct routing, parasitic inductance can be kept small. GND layers might be used for shielding if the parasitic capacitance can be kept small. Routing the SENSE+ and SENSE- close to each other minimizes inductive noise injection. Keep these traces away from switching nodes and swiftly alternating signal lines such as the I<sup>2</sup>C bus.

Improper layout might show the symptoms of poor line or load regulation, ground and output voltage shifts, stability issues or unsatisfying EMI behavior.

See Figure 48 for the recommended layout.

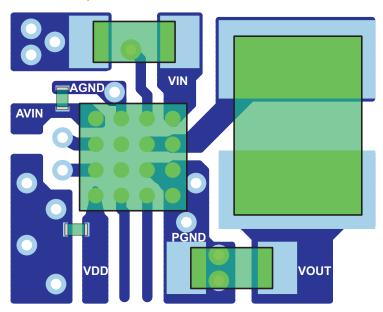


Figure 48. Layout Suggestion (top view). Overall Solution Size: 27.5mm<sup>2</sup>



### **REGISTER SETTINGS**

### Overview

### Table 9. TPS62360 Register Settings Overview

		RESET /	READ /			REGI	STER (defa	ult / reset val	ues)		
ADDRESS	REGISTER	DEFAULT	WRITE	MSB							LSB
		STATE		D7	D6	D5	D4	D3	D2	D1	D0
0x00h	SET0	0x111111	R/W	MODE0				OV0	[5:0]		
0x01h	SET1	0x010111	R/W	MODE1	1 OV1[5:0]						
0x02h	SET2	0x111111	R/W	MODE2	MODE2 OV2[5:0]						
0x03h	SET3	0x100001	R/W	MODE3		OV3[5:0]					
0x04h	Ctrl	111xxxxx	R/W	PD_EN	PD_VSEL0	PD_VSEL1					
0x05h	Temp	xxxxx000	R/W						DIS_TS	TJEW	TJTS
0x06h	RmpCtrl	000xx00x	R/W		RMP[2:0]				EN_DISC	RAMP_PFM	
0x07h	(Reserved)	xxxxxxx									
0x08h	Chip_ID	100000xx	R								
0x09h	Chip_ID	TOOOOOXX	K								

### Table 10. TPS62361B Register Settings Overview

ADDRESS	REGISTER	RESET / DEFAULT		DEFAULT	DEFAULT			DEFAULT	READ / WRITE	MSB		REGI	STER (defa	ult / reset val	ues)		LSB
		STATE	WKIIE	D7	D6	D5	D4	D3	D2	D1	D0						
0x00h	SET0	00101110	R/W	MODE0				OV0[6:0]									
0x01h	SET1	01011010	R/W	MODE1				OV1[6:0]									
0x02h	SET2	01000010	R/W	MODE2	MODE2 OV2[6:0]												
0x03h	SET3	01000010	R/W	MODE3				OV3[6:0]									
0x04h	Ctrl	111xxxxx	R/W	PD_EN	PD_VSEL0	PD_VSEL1											
0x05h	Temp	xxxxx000	R/W						DIS_TS	TJEW	TJTS						
0x06h	RmpCtrl	000xx00x	R/W		RMP[2:0]				EN_DISC	RAMP_PFM							
0x07h	(Reserved)	XXXXXXX															
0x08h	Chip_ID	100001xx	R														
0x09h	Chip_ID	TOUOUTXX	K														

### Table 11. TPS62362 Register Settings Overview

		RESET /	2542 /			REGI	STER (defau	It / reset valu	ues)		
ADDRESS	REGISTER	DEFAULT	READ / WRITE	MSB							LSB
		STATE	E   *******	D7	D6	D5	D4	D3	D2	D1	D0
0x00h	SET0	0x101110	R/W	MODE0			OV0[5:0]				
0x01h	SET1	0x010111	R/W	MODE1		OV1[5:0]					
0x02h	SET2	0x101011	R/W	MODE2		OV2[5:0]					
0x03h	SET3	0x100001	R/W	MODE3				OV3[	[5:0]		
0x04h	Ctrl	111xxxxx	R/W	PD_EN	PD_VSEL0	PD_VSEL1					
0x05h	Temp	xxxxx000	R/W						DIS_TS	TJEW	TJTS
0x06h	RmpCtrl	000xx00x	R/W		RMP[2:0]				EN_DISC	RAMP_PFM	
0x07h	(Reserved)	xxxxxxx									
0x08h	Chip_ID	10001000	R								
0x09h	Chip_ID	100010xx	K								

### Register 0x00h Description: SET0

The register settings apply by choosing SET0 ( VSEL1 = LOW, VSEL0 = LOW).

### Table 12. TPS62360 Register 0x00h Description

REG	REGISTER ADDRESS: 0x00h Read/Write															
BIT	NAME	DEFA	ULT		1	DESCRIPTION										
D7	MODE0	MSB	0	0 = PFM / F	Operation mode for SET0 0 = PFM / PWM mode operation 1 = Forced PWM mode operation											
D6			х	Reserved for	Reserved for future use											
D5			1	Output voltage for SET0 Default: (111111) <sub>2</sub> = 1.4V												
D4			1	D5-D0 Output voltage												
D3			1	00 0000	770 mV											
D2	OV0[5:0]		ļ			-					Ė	-	1	00 0001	780 mV	
DZ	0.0[0.0]		1	00 0010	790 mV											
D1			4													
וט				11 1111	1400 mV											
D0		LSB	1	$V_{OUT} = (xx xxxx)_2 \times 10 \text{mV} + 770 \text{ mV}$												

### Table 13. TPS62361B Register 0x00h Description

REGISTER ADDRESS: 0x00h Read/Write										
BIT	NAME	DEFAULT			DESCRIPTION					
D7	MODE0	MSB	0	Operation mode for SET0 0 = PFM / PWM mode operation 1 = Forced PWM mode operation						
D6			0		age for SET0					
D5			1	Default: (01	Default: $(0101110)_2 = 0.96V$					
D4			0	D6-D0	Output voltage					
D3			1	000 0000	500 mV					
D2	OV0[6:0]		4	000 0001	510 mV					
DZ				000 0010	520 mV					
D1			1							
וט				111 1111	1770 mV					
D0		LSB	0	V <sub>OUT</sub> = (xxx	( xxxx) <sub>2</sub> × 10mV + 500 mV					

### Table 14. TPS62362 Register 0x00h Description

REGISTER ADDRESS: 0x00h Read/Write								
BIT	NAME	DEFA	ULT	DESCRIPTION				
D7	MODE0	MSB 0		Operation mode for SET0 0 = PFM / PWM mode operation 1 = Forced PWM mode operation				
D6			Х	Reserved for future use				



### Table 14. TPS62362 Register 0x00h Description (continued)

REGISTER ADDRESS: 0x00h Read/Write								
BIT	NAME	DEFA	ULT	DESCRIPTION				
D5			1		age for SET0 11110) <sub>2</sub> = 1.23V			
D4			0	D5-D0	Output voltage			
D3			1	00 0000	770 mV			
D2	OV0[5:0]	0[5:0]	4	00 0001	780 mV			
D2	0.0[0.0]		'	00 0010	790 mV			
D1			1					
וט			'	11 1111	1400 mV			
D0		LSB	0	V <sub>OUT</sub> = (xx	xxxx) <sub>2</sub> × 10mV + 770 mV			

### Register 0x01h Description: SET1

The register settings apply by choosing SET1 ( VSEL1 = LOW, VSEL0 = HIGH).

### Table 15. TPS62360 Register 0x01h Description

REGISTER ADDRESS: 0x01h Read/Write								
BIT	NAME	DEFA	ULT			DESCRIPTION		
D7	MODE1	MSB	0	Operation mode for SET1 0 = PFM / PWM mode operation 1 = Forced PWM mode operation				
D6			х	Reserved for future use				
D5			0	Output volta Default: (01	age for SET1   0111) <sub>2</sub> = 1.0V			
D4			1	D5-D0	Output voltage			
D3			0	00 0000	770 mV			
D2	OV1[5:0]	I	4	00 0001	780 mV			
DZ	0 1 1[0.0]		ı	00 0010	790 mV			
D1			1					
וט			ı	11 1111	1400 mV			
D0		LSB	1	V <sub>OUT</sub> = (xx	xxxx) <sub>2</sub> × 10mV + 770 mV			

### Table 16. TPS62361B Register 0x01h Description

REG	REGISTER ADDRESS: 0x01h Read/Write								
BIT	NAME	DEFAULT			DESCRIPTION				
D7	MODE1	MSB	0	Operation mode for SET1 0 = PFM / PWM mode operation 1 = Forced PWM mode operation					
D6			1		age for SET1				
D5			0	Default: (10	$(0.011010)_2 = 1.4V$				
D4			1	D6-D0	Output voltage				
D3			1	000 0000	500 mV				
D2	OV1[6:0]		0	000 0001	510 mV				
DZ				000 0010	520 mV				
D1			1						
וט			'	111 1111	1770 mV				
D0		LSB	0	V <sub>OUT</sub> = (xxx	( xxxx) <sub>2</sub> × 10mV + 500 mV				

### Table 17. TPS62362 Register 0x01h Description

REGISTER ADDRESS: 0x01h Read/Write								
BIT	NAME	DEFA	ULT	DESCRIPTIO	N			
D7	MODE1	MSB	0	Operation mode for SET1 0 = PFM / PWM mode operation 1 = Forced PWM mode operation				
D6			х	Reserved for future use				



## Table 17. TPS62362 Register 0x01h Description (continued)

REG	REGISTER ADDRESS: 0x01h Read/Write												
BIT	NAME	DEFA	ULT		DESCRIPTION								
D5			0	Output volta Default: (01	age for SET1 0111) <sub>2</sub> = 1.0V								
D4			1	D5-D0	Output voltage								
D3			0	00 0000	770 mV								
D2	OV1[5:0]	1[5:0]								4	00 0001	780 mV	
D2	011[0.0]		1	00 0010	790 mV								
D1							4						
וט			1	11 1111	1400 mV								
D0		LSB	1	$V_{OUT} = (xx$	xxxx) <sub>2</sub> × 10mV + 770 mV								

## Register 0x02h Description: SET2

The register settings apply by choosing SET2 ( VSEL1 = HIGH, VSEL0 = LOW).

#### Table 18. TPS62360 Register 0x02h Description

REG	REGISTER ADDRESS: 0x02h Read/Write																				
BIT	NAME	DEFA	ULT			DESCRIPTION															
D7	MODE2	MSB	0	0 = PFM / I	Operation mode for SET2 0 = PFM / PWM mode operation 1 = Forced PWM mode operation																
D6			х	Reserved f	or future use																
D5			1	Output voltage for SET2 Default: (010111) <sub>2</sub> = 1.4V																	
D4			1	D5-D0	Output voltage																
D3			1	00 0000	770 mV																
D2	OV2[5:0]	-01																1	00 0001	780 mV	
D2	0 12[0.0]		ı	00 0010	790 mV																
D1		1																			
וט			ı	11 1111 1400 mV																	
D0		LSB	1	V <sub>OUT</sub> = (xx	xxxx) <sub>2</sub> × 10mV + 770 mV																

## Table 19. TPS62361B Register 0x02h Description

REG	REGISTER ADDRESS: 0x02h Read/Write																							
BIT	NAME	DEFA	DEFAULT DESCRIPTION			SCRIPTION																		
D7	MODE2	MSB	0	0 = PFM / P	Operation mode for SET2 0 = PFM / PWM mode operation 1 = Forced PWM mode operation																			
D6			1		ige for SET2																			
D5			0	Default: (10	$00010)_2 = 1.16V$																			
D4				0	D6-D0	Output voltage																		
D3			0	000 0000	500 mV																			
D2	OV2[6:0]	2[6:0]				<u> </u>	ļ	ļ			ļ										0	000 0001	510 mV	
D2					0	000 0010	520 mV																	
D4																								
D1			ı	111 1111	1770 mV																			
D0		LSB	0	V <sub>OUT</sub> = (xxx	xxxx) <sub>2</sub> × 10mV + 500 mV																			

#### Table 20. TPS62362 Register 0x02h Description

REG	REGISTER ADDRESS: 0x02h Read/Write							
BIT	NAME	DEFAULT		DESCRIPTION				
D7	MODE2	MSB	0	Operation mode for SET2 0 = PFM / PWM mode operation 1 = Forced PWM mode operation				
D6			Х	Reserved for future use				



## Table 20. TPS62362 Register 0x02h Description (continued)

REG	REGISTER ADDRESS: 0x02h Read/Write											
BIT	NAME	DEFA	ULT			DESCRIPTION						
D5			1		age for SET2 01011) <sub>2</sub> = 1.2V							
D4			0	D5-D0	Output voltage							
D3		[5:0]				1	00 0000	770 mV				
D2	OV2[5:0]										0	00 0001
D2	0.7=[0.0]			0	00 0010	790 mV						
D1									1			
וט	!			11 1111	1400 mV							
D0		LSB	1	$V_{OUT} = (xx)$	xxxx) <sub>2</sub> × 10mV + 770 mV							

## Register 0x03h Description: SET3

The register settings apply by choosing SET3 ( VSEL1 = HIGH, VSEL0 = HIGH).

#### Table 21. TPS62360 Register 0x03h Description

REG	REGISTER ADDRESS: 0x03h Read/Write																		
BIT	NAME	DEFA	ULT			DESCRIPTION													
D7	MODE3	MSB	0	0 = PFM / I	Operation mode for SET3 0 = PFM / PWM mode operation 1 = Forced PWM mode operation														
D6			х	Reserved f	or future use														
D5			1	Output voltage Default: (10	age for SET3 00001) <sub>2</sub> = 1.1V														
D4			0	D5-D0	Output voltage														
D3			0	00 0000	770 mV														
D2	OV3[5:0]															0	00 0001	780 mV	
D2	0 10[0.0]		U	00 0010	790 mV														
D1												0							
וט				11 1111	1400 mV														
D0		LSB	1 V <sub>OUT</sub> = (xx xxxx) <sub>2</sub> × 10mV + 770 mV																

## Table 22. TPS62361B Register 0x03h Description

REG	REGISTER ADDRESS: 0x03h Read/Write																	
BIT	NAME	DEFA	ULT		DESC	CRIPTION												
D7	MODE3	MSB	0	0 = PFM / F	Operation mode for SET3 0 = PFM / PWM mode operation 1 = Forced PWM mode operation													
D6			1		age for SET3													
D5			0	Default: (10	$00010)_2 = 1.16V$													
D4			0	D6-D0	Output voltage													
D3			0	000 0000	500 mV													
<b>D</b> 0	OV3[6:0]		ļ		 		ļ		ļ	ļ				ļ	0	000 0001	510 mV	
D2			0	000 0010	520 mV													
-																		
D1			1	111 1111	1770 mV													
D0		LSB	0	$V_{OUT} = (xxx)$	$V_{OUT} = (xxx xxxx)_2 \times 10 \text{mV} + 500 \text{ mV}$													

# Table 23. TPS62362 Register 0x03h Description

REG	REGISTER ADDRESS: 0x03h Read/Write							
BIT	NAME	DEFAULT		DESCRIPTION				
D7	MODE3	MSB	0	Operation mode for SET3 0 = PFM / PWM mode operation 1 = Forced PWM mode operation				
D6			Х	Reserved for future use				



## Table 23. TPS62362 Register 0x03h Description (continued)

REG	REGISTER ADDRESS: 0x03h Read/Write											
BIT	NAME	DEFA	ULT			DESCRIPTION						
D5			1		age for SET3 00001) <sub>2</sub> = 1.1V							
D4			0	D5-D0	Output voltage							
D3					0	00 0000	770 mV					
D2	OV3[5:0]									0	00 0001	780 mV
D2	0.0[0.0]			0	00 0010	790 mV						
D1							0					
וט	!		0	11 1111	1400 mV							
D0		LSB	1	$V_{OUT} = (xx$	xxxx) <sub>2</sub> × 10mV + 770 mV							

# Register 0x04h Description: Ctrl

## Table 24. TPS6236x Register 0x04h Description

REGIST	REGISTER ADDRESS: 0x04h Read / Write							
BIT	NAME	DEFA	ULT	DESCRIPTION				
D7	PD_EN	MSB	1	EN internal pull down resistor 0 = disabled 1 = enabled				
D6	PD_VSEL0		1	VSEL0 internal pull down resistor 0 = disabled 1 = enabled				
D5	PD_VSEL1		1	VSEL1 internal pull down resistor 0 = disabled 1 = enabled				
D4			Х	Reserved for future use				
D3			х	Reserved for future use				
D2			Х	Reserved for future use				
D1			Х	Reserved for future use				
D0		LSB	Х	Reserved for future use				

# Register 0x05h Description: Temp

## Table 25. TPS6236x Register 0x05h Description

REGISTER ADDRESS: 0x05h Read/Write							
BIT	NAME	DEFA	ULT	DESCRIPTION			
D7		MSB	х	Reserved for future use			
D6			Х	Reserved for future use			
D5			Х	Reserved for future use			
D4			Х	Reserved for future use			
D3			Х	Reserved for future use			
D2	DIS_TS		0	Disable temperature shutdown feature  0 = Temperature shutdown enabled  1 = Temperature shutdown disabled			
D1	TJEW		0	$T_J$ early warning bit $0 = T_J < 120^{\circ}C$ (typ) $1 = T_J \ge 120^{\circ}C$ (typ)			
D0	TJTS		0	T <sub>J</sub> temperature shutdown bit 0 = die temperature within the valid range 1 = temperature shutdown was triggered			
		LSB		Bit needs to be reset after it has been latched.			



# Register 0x06h Description: RmpCtrl

## Table 26. TPS6236x Register 0x06h Description

REG	REGISTER ADDRESS: 0x06h Read/Write									
BIT	NAME	DEFAL	JLT	DESCRIPTION						
		MSB		Output vol	tage ramp timing					
D7			0	D7-D5	Slope					
				000	32 mV / µs					
				001	16 mV / µs					
				010	8 mV / µs					
D6	RMP[2:0]		0							
				110	0.5 mV / µs					
				111	0.25 mV / µs					
D5			0	$\frac{\Delta V_{OUT}}{\Delta t}$	$\frac{1}{\mu s} = 32 \frac{mV}{\mu s} \frac{1}{2^{(RMP[2-0])_2}}$					
D4			х	Reserved	for future use					
D3			х	Reserved	for future use					
D2	EN_DISC		0	0 = disable	Active output capacitor discharge at shutdown 0 = disabled 1 = enabled					
D1	RAMP_PFM		0	0 = output	Defines the ramp behavior if the device is in Power Save (PFM) mode 0 = output cap will be discharged by the load 1 = output voltage will be forced to follow the ramp down slope					
D0		LSB	х	Reserved	for future use					

# Register 0x07h Description: (Reserved)

## Table 27. TPS6236x Register 0x07h Description

REGISTE	REGISTER ADDRESS: 0x07h								
BIT	NAME	DEFA	ULT	DESCRIPTION					
D7		MSB	х	Reserved for future use					
D6			х	Reserved for future use					
D5			х	Reserved for future use					
D4			х	Reserved for future use					
D3			х	Reserved for future use					
D2			х	Reserved for future use					
D1			х	Reserved for future use					
D0		LSB	Х	Reserved for future use					

# Register 0x08h, 0x09h Description Chip\_ID:

## Table 28. TPS6236x Register 0x08h and 0x09h Description

REGI	REGISTER ADDRESS: 0x08h, 0x09 Read										
BIT	NAME	DEFA	ULT	DESCRIPTION							
D7		MSB	1								
D6			0	Variation ID	V 1 15						
D5			0	Vendor ID							
D4			0								
D3			х	D3-D2	Part number ID						
				00	TPS62360						
D2	D2		х	01	TPS62361B						
				10	TPS62362						
D1			х	D1-D0	Chip revision ID						
				00	Rev. 1						
				01	Rev. 2						
D0			Х	10	Rev. 3						
		LSB		11	Rev. 4						



#### **PACKAGE SUMMARY**

**CHIP SCALE PACKAGE** (TOP VIEW) Code: • TI — Texas Instruments **TIYMLLLLS** • YM — Year Month date code E XXXXXXXX • LLLL — Lot trace code • S — Assembly site code XXXXXXXX — Part number • TPS62360 = TPS62360 • TPB62361 = TPS62361B : A1: • TPS62362 = TPS62362 D

Figure 49. Package Marking and Dimensions

#### **CHIP SCALE PACKAGE DIMENSIONS**

The TPS6236x device is available in a 16-bump chip scale package (YZH, NanoFree™). The package dimensions are given as:

- D = 2.076mm (+/- 0.01mm)
- E = 2.076mm (+/- 0.01mm)





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#### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
TPS62360YZHR	ACTIVE	DSBGA	YZH	16	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TPS62360YZHT	ACTIVE	DSBGA	YZH	16	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	
TPS62361BYZHR	ACTIVE	DSBGA	YZH	16	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	
TPS62361BYZHT	ACTIVE	DSBGA	YZH	16	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	
TPS62362YZHR	PREVIEW	DSBGA	YZH	16	3000	TBD	Call TI	Call TI	
TPS62362YZHT	PREVIEW	DSBGA	YZH	16	250	TBD	Call TI	Call TI	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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13-Jun-2011

## PACKAGE MATERIALS INFORMATION

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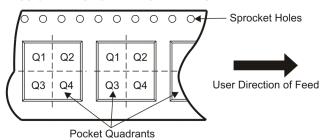
## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

All differsions are norminal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS62360YZHR	DSBGA	YZH	16	3000	180.0	8.4	2.18	2.18	0.81	4.0	8.0	Q1
TPS62360YZHT	DSBGA	YZH	16	250	180.0	8.4	2.18	2.18	0.81	4.0	8.0	Q1
TPS62361BYZHR	DSBGA	YZH	16	3000	180.0	8.4	2.18	2.18	0.81	4.0	8.0	Q1
TPS62361BYZHT	DSBGA	YZH	16	250	180.0	8.4	2.18	2.18	0.81	4.0	8.0	Q1

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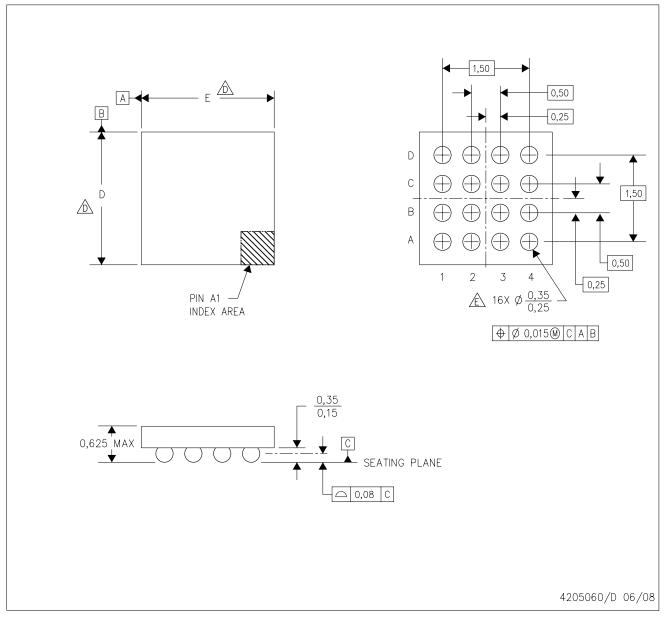


\*All dimensions are nominal

7 till dillitoriolorio di o mominidi							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS62360YZHR	DSBGA	YZH	16	3000	190.5	212.7	31.8
TPS62360YZHT	DSBGA	YZH	16	250	190.5	212.7	31.8
TPS62361BYZHR	DSBGA	YZH	16	3000	190.5	212.7	31.8
TPS62361BYZHT	DSBGA	YZH	16	250	190.5	212.7	31.8

# YZH (S-XBGA-N16)

## DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- Devices in YZH package can have dimension D ranging from 1.94 to 2.65 mm and dimension E ranging from 1.94 to 2.65 mm.

  To determine the exact package size of a particular device, refer to the device datasheet or contact a local TI representative.
- E. Reference Product Data Sheet for array population. 4 x 4 matrix pattern is shown for illustration only.
- F. This package contains lead—free balls. Refer to YEH (Drawing #4204183) for tin—lead (SnPb) balls.

NanoFree is a trademark of Texas Instruments.



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